## **MJE344G**

# Plastic NPN Silicon Medium-Power Transistor

This device is useful for medium voltage applications requiring high  $f_T$  such as converters and extended range amplifiers.

#### **Features**

• These Devices are Pb-Free and are RoHS Compliant\*

#### **MAXIMUM RATINGS**

| Rating  | Symbol                            | Value       | Unit       |
|---|-----------------------------------|-------------|------------|
| Collector-Emitter Voltage   | $V_{CEO}$                         | 200         | Vdc        |
| Collector-Base Voltage  | V <sub>CB</sub>                   | 200         | Vdc        |
| Emitter Base Voltage  | V <sub>EB</sub>                   | 5.0         | Vdc        |
| Collector Current – Continuous                                    | I <sub>C</sub>                    | 500         | mAdc       |
| Base Current  | I <sub>B</sub>                    | 250         | mAdc       |
| Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C | P <sub>D</sub>                    | 20<br>0.16  | W<br>mW/°C |
| Operating and Storage Junction<br>Temperature Range               | T <sub>J</sub> , T <sub>stg</sub> | -65 to +150 | °C         |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

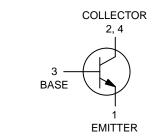
| Characteristic                       | Symbol            | Max  | Unit |
|--------------------------------------|-------------------|------|------|
| Thermal Resistance, Junction-to-Case | $\theta_{\sf JC}$ | 6.25 | °C/W |



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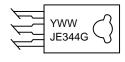
http://onsemi.com

# 0.5 AMPERE POWER TRANSISTORS NPN SILICON 150-200 VOLTS, 20 WATTS





#### MARKING DIAGRAM



Y = Year WW = Work Week JE344 = Device Code G = Pb-Free Package

#### ORDERING INFORMATION

| Device  | Package             | Shipping      |
|---------|---------------------|---------------|
| MJE344G | TO-225<br>(Pb-Free) | 500 Units/Box |

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

| Characteristic  | Symbol                | Min | Max | Unit |
|---|-----------------------|-----|-----|------|
| OFF CHARACTERISTICS   |                       |     |     |      |
| Collector–Emitter Sustaining Voltage (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0)              | V <sub>CEO(sus)</sub> | 200 | -   | Vdc  |
| Collector Cutoff Current (V <sub>CE</sub> = 200 Vdc, I <sub>B</sub> = 0)                          | I <sub>CEO</sub>      | -   | 1.0 | mAdc |
| Collector Cutoff Current (V <sub>CB</sub> = 200 Vdc, I <sub>E</sub> = 0)                          | I <sub>CBO</sub>      | -   | 0.1 | mAdc |
| Emitter Cutoff Current (V <sub>EB</sub> = 5.0 Vdc, I <sub>C</sub> = 0)                            | I <sub>EBO</sub>      | -   | 0.1 | mAdc |
| ON CHARACTERISTICS  |                       |     |     |      |
| DC Current Gain (I <sub>C</sub> = 50 mAdc, V <sub>CE</sub> = 10 Vdc)                              | h <sub>FE</sub>       | 30  | 300 | -    |
| Collector–Emitter Saturation Voltage (I <sub>C</sub> = 50 mAdc, I <sub>B</sub> = 5.0 mAdc)        | V <sub>CE(sat)</sub>  | _   | 1.0 | Vdc  |
| Base–Emitter On Voltage (I <sub>C</sub> = 50 mAdc, V <sub>CE</sub> = 10 Vdc)                      | V <sub>BE(on)</sub>   | _   | 1.0 | Vdc  |
| DYNAMIC CHARACTERISTICS   |                       |     |     |      |
| Current-Gain - Bandwidth Product (I <sub>C</sub> = 50 mAdc, V <sub>CE</sub> = 25 Vdc, f = 10 MHz) | f <sub>T</sub>        | 15  | -   | MHz  |
| Output Capacitance (V <sub>CB</sub> = 20 Vdc, I <sub>E</sub> = 0, f = 100 kHz)                    | C <sub>ob</sub>       | -   | 15  | pF   |
| Small–Signal Current Gain (I <sub>C</sub> = 50 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)       | h <sub>fe</sub>       | 25  | _   | _    |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

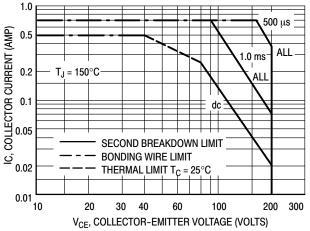
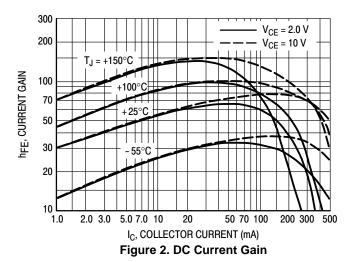


Figure 1. Active Region Safe Operating Area

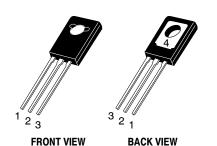
There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation then the curves indicate.

The data of Figure 1 is based on  $T_{J(pk)} = 150^{\circ}C$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \le 150^{\circ}C$ . At high case temperatures, thermal limitations will reduce the power that can be handled to values less then the limitations imposed by second breakdown.



1.0 0.8  $V_{BE(sat)} @ I_C/I_B = 10$ VOLTAGE (VOLTS) V<sub>BE</sub> @ V<sub>CE</sub> = 10 V 0.4  $V_{CE(sat)} @ I_C/I_B = 10$ 0.2  $T_J = +25^{\circ}C$  $I_{C}/I_{B} = 5.0$ 10 20 50 200 300 I<sub>C</sub>, COLLECTOR CURRENT (mA) Figure 3. "On" Voltages

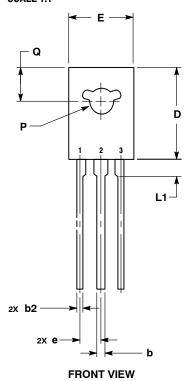


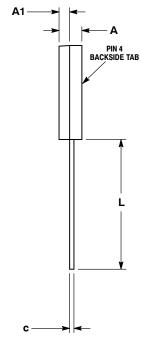


TO-225 CASE 77-09 **ISSUE AD** 

**DATE 25 MAR 2015** 

#### SCALE 1:1





**SIDE VIEW** 

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

  2. CONTROLLING DIMENSION: MILLIMETERS.

  3. NUMBER AND SHAPE OF LUGS OPTIONAL.

|     | MILLIMETERS  |       |  |  |  |
|-----|--------------|-------|--|--|--|
| DIM | MIN          | MAX   |  |  |  |
| Α   | 2.40         | 3.00  |  |  |  |
| A1  | 1.00         | 1.50  |  |  |  |
| b   | 0.60         | 0.90  |  |  |  |
| b2  | 0.51         | 0.88  |  |  |  |
| С   | 0.39         | 0.63  |  |  |  |
| D   | 10.60        | 11.10 |  |  |  |
| E   | 7.40         | 7.80  |  |  |  |
| е   | 2.04         | 2.54  |  |  |  |
| L   | L 14.50 16.0 |       |  |  |  |
| L1  | 1.27         | 2.54  |  |  |  |
| P   | 2.90         | 3.30  |  |  |  |
| Q   | 3.80 4.20    |       |  |  |  |

#### **GENERIC MARKING DIAGRAM\***



= Year

ww = Work Week

XXXXX = Device Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

| STYLE 1:<br>PIN 1.<br>2., 4.<br>3. | EMITTER<br>COLLECTOR<br>BASE | STYLE 2:<br>PIN 1.<br>2., 4.<br>3. | STYLE 3:<br>PIN 1.<br>2., 4.<br>3. | BASE<br>COLLECTOR<br>EMITTER | STYLE 4:<br>PIN 1.<br>2., 4.<br>3. | ANODE 1<br>ANODE 2<br>GATE | 2., 4.                              | MT 1<br>MT 2<br>GATE |
|------------------------------------|------------------------------|------------------------------------|------------------------------------|------------------------------|------------------------------------|----------------------------|-------------------------------------|----------------------|
| STYLE 6:<br>PIN 1.<br>2., 4.<br>3. | CATHODE<br>GATE<br>ANODE     | STYLE 7:<br>PIN 1.<br>2., 4.<br>3. | STYLE 8:<br>PIN 1.<br>2., 4.<br>3. | SOURCE<br>GATE<br>DRAIN      | STYLE 9:<br>PIN 1.<br>2., 4.<br>3. | GATE<br>DRAIN<br>SOURCE    | STYLE 10:<br>PIN 1.<br>2., 4.<br>3. | SOURCE<br>DRAIN      |

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|------------------|-------------|--|-------------|--|--|
| DESCRIPTION:     | TO-225      |  | PAGE 1 OF 1 |  |  |

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